

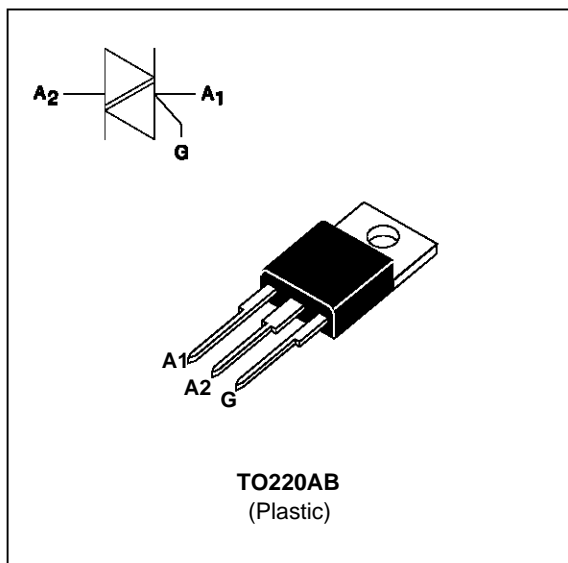
STANDARD TRIACS

FEATURES

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION : $(dV/dt)_c > 10V/\mu s$

DESCRIPTION

The BTB24 B triac family are high performance glass passivated PNPN devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	$T_c = 80\text{ }^\circ\text{C}$ 25	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 8.3\text{ ms}$	210
		$t_p = 10\text{ ms}$	200
I^2t	I^2t value	$t_p = 10\text{ ms}$ 200	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : $I_G = 500\text{mA}$ $di_G/dt = 1\text{A}/\mu\text{s}$	Repetitive $F = 50\text{ Hz}$	10
		Non Repetitive	50
T_{stg} T_j	Storage and operating junction temperature range	- 40 to + 150 - 40 to + 125	$^\circ\text{C}$ $^\circ\text{C}$
T_l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case	260	$^\circ\text{C}$

Symbol	Parameter	BTB24-... B				Unit
		400	600	700	800	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125\text{ }^\circ\text{C}$	400	600	700	800	V

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	°C/W
Rth (j-c) DC	Junction to case for DC	1.7	°C/W
Rth (j-c) AC	Junction to case for 360° conduction angle (F = 50 Hz)	1.3	°C/W

GATE CHARACTERISTICS (maximum values)

 $P_G (AV) = 1W$ $P_{GM} = 10W$ (tp = 20 μs) $I_{GM} = 4A$ (tp = 20 μs) $V_{GM} = 16V$ (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix	Unit
					B	
IGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III	MAX	50	mA
			IV	MAX	100	
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	I-II-III-IV	MAX	1.5	V
VGD	VD=VDRM RL=3.3kΩ	Tj=125°C	I-II-III-IV	MIN	0.2	V
tgt	VD=VDRM IG = 500mA dIG/dt = 3A/μs	Tj=25°C	I-II-III-IV	TYP	2.5	μs
IL	IG=1.2 IGT	Tj=25°C	I-III-IV	TYP	40	mA
			II		70	
IH *	IT= 500mA gate open	Tj=25°C		MAX	50	mA
VTM *	ITM= 35A tp= 380μs	Tj=25°C		MAX	1.8	V
IDRM IRRM	VDRM Rated VRRM Rated	Tj=25°C		MAX	0.01	mA
		Tj=125°C		MAX	2	
dV/dt *	Linear slope up to VD=67%VDRM gate open	Tj=125°C		MIN	250	V/μs
(dV/dt)c *	(dI/dt)c = 11.1A/ms	Tj=125°C		MIN	10	V/μs

* For either polarity of electrode A2 voltage with reference to electrode A1.

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

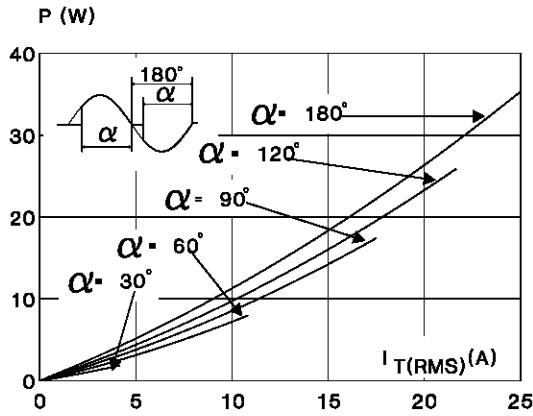


Fig.3 : RMS on-state current versus case temperature.

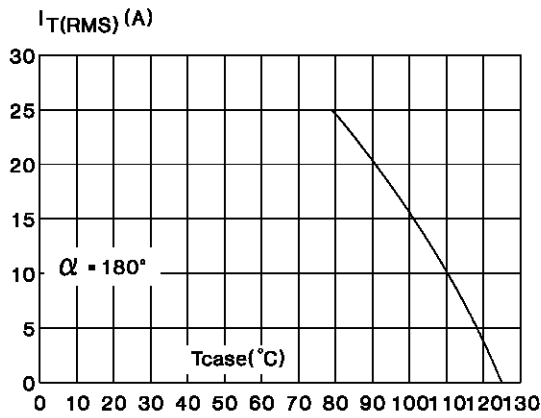


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

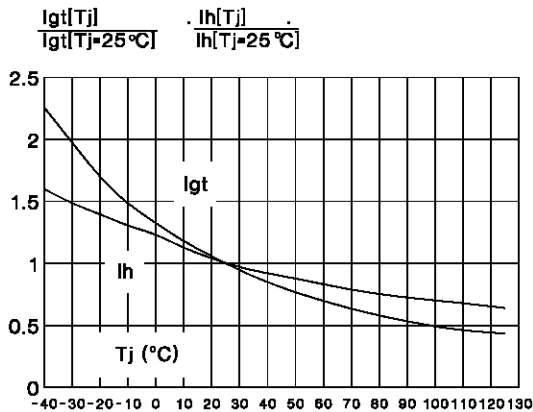


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

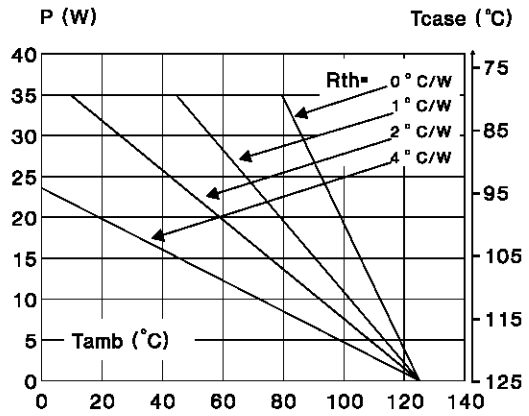


Fig.4 : Relative variation of thermal impedance versus pulse duration.

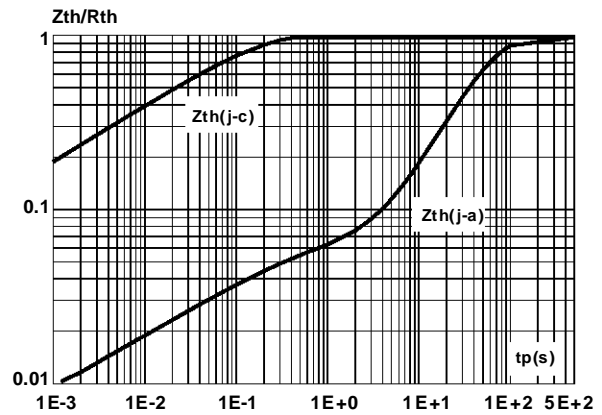


Fig.6 : Non Repetitive surge peak on-state current versus number of cycles.

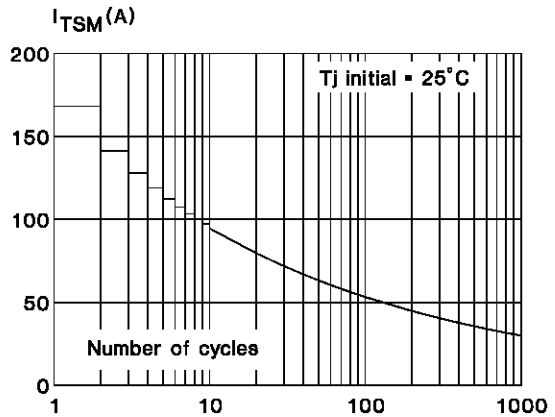


Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

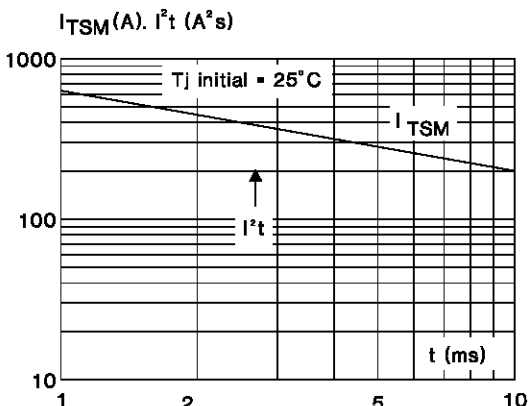
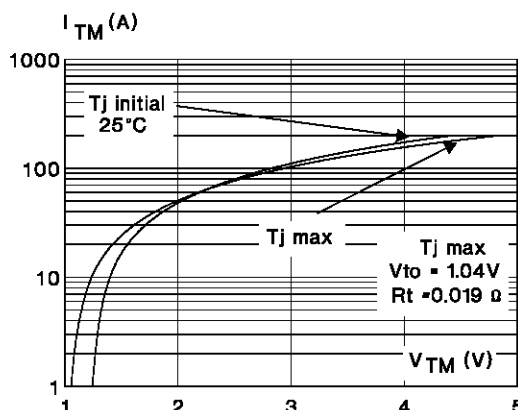


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO220AB Plastic

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10.20	10.50	0.401	0.413
B	14.23	15.87	0.560	0.625
C	12.70	14.70	0.500	0.579
D	5.85	6.85	0.230	0.270
F		4.50		0.178
G	2.54	3.00	0.100	0.119
H	4.48	4.82	0.176	0.190
I	3.55	4.00	0.140	0.158
J	1.15	1.39	0.045	0.055
L	0.35	0.65	0.013	0.026
M	2.10	2.70	0.082	0.107
N	4.58	5.58	0.18	0.22
O	0.80	1.20	0.031	0.048
P	0.64	0.96	0.025	0.038

Cooling method : C
 Marking : type number
 Weight : 2.3 g

Recommended torque value : 0.8 m.N.
 Maximum torque value : 1 m.N.

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